	Application No.	Applicant(s)	——У
Notice of Allowability	10/619,052	FISHBURN ET AL.	
	Examiner	Art Unit	
	Lan Vinh	1765	
	Lan viiii	1765	
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT IN of the Office or upon petition by the applicant. See 37 CFR 1.31	S (OR REMAINS) CLOSED in the community of the community o	n this application. If not included unication will be mailed in due course. The	1IS itiative
1. \square This communication is responsive to <u>Amendment and res</u>	sponse filed on 4/7/2006.		
2. The allowed claim(s) is/are 1-17 and 21-38.			
3. Acknowledgment is made of a claim for foreign priority u	under 35 U.S.C. § 119(a)-(d)	or (f).	
a) ☐ All b) ☐ Some* c) ☐ None of the:			
 Certified copies of the priority documents have 	e been received.		
Certified copies of the priority documents have	e been received in Application	on No	
Copies of the certified copies of the priority de	ocuments have been receive	ed in this national stage application from the	he
International Bureau (PCT Rule 17.2(a)).			
* Certified copies not received:			
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONI THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	" of this communication to file MENT of this application.	e a reply complying with the requirements	;
4. A SUBSTITUTE OATH OR DECLARATION must be subr INFORMAL PATENT APPLICATION (PTO-152) which give	nitted. Note the attached EX ves reason(s) why the oath o	AMINER'S AMENDMENT or NOTICE OF r declaration is deficient.	:
5. CORRECTED DRAWINGS (as "replacement sheets") mu	ıst be submitted.		
(a) I including changes required by the Notice of Draftsper		w (PTO-948) attached	
1) 🗌 hereto or 2) 🔲 to Paper No./Mail Date		,	
(b) ☐ including changes required by the attached Examiner Paper No./Mail Date	's Amendment / Comment o	r in the Office action of	
Identifying indicia such as the application number (see 37 CFR each sheet. Replacement sheet(s) should be labeled as such in	1.84(c)) should be written on t the header according to 37 Cl	he drawings in the front (not the back) of FR 1.121(d).	
6. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT	osit of BIOLOGICAL MAT FOR THE DEPOSIT OF BI	ERIAL must be submitted. Note the OLOGICAL MATERIAL.	
Attachment(s)	5 There are	faces I Data A.A. H. H. (DTD 450)	
 Notice of References Cited (PTO-892) Dotice of Draftperson's Patent Drawing Review (PTO-948) 	_	formal Patent Application (PTO-152)	
	Paper No.	ummary (PTO-413), /Mail Date	
 Information Disclosure Statements (PTO-1449 or PTO/SB/ Paper No./Mail Date 	08), 7. ☐ Examiner's	Amendment/Comment	
Examiner's Comment Regarding Requirement for Deposit of Biological Material	8. 🛭 Examiner's	Statement of Reasons for Allowance	
•	9.	∴	
		Lan Vinh AU 1765	

Application/Control Number: 10/619,052

Art Unit: 1765

DETAILED ACTION

Allowable Subject Matter

1. Claims 1-17, 21-38 allowed.

The following is an examiner's statement of reasons for allowance:

Regarding claim 1, the applicants have presented a persuasive argument, see page 15 of the response filed on 4/7/2006, that the cited prior art of Chiang fails to disclose a step of forming a first dielectric spacer on the at least one dielectric layer and on the first conductive layer of the first sidewall and a second dielectric spacer on the at least one dielectric layer and on the first conductive layer of the second sidewall to cause an upper surface of each sidewall to extend above an upper surface of the first and second spacers, in combination with the rest of the limitations of claim 1. Regarding claim 24, the cited prior art of record fails to disclose or suggest a method for forming a semiconductor device comprises a step of forming a first conductive layer, a first silicon dioxide layer on the first conductive layer, a silicon nitride layer on the first silicon dioxide layer, and a second silicon dioxide layer on the silicon nitride layer, in combination with the rest of the limitations of claim 24. Regarding claim 30, the cited prior art of record fails to disclose or suggest a method for forming a semiconductor device comprises a step of removing the second conductive layer from over an entire width of the first conductive layer and leaving the second conductive layer at other locations, in combination with the rest of the limitations of claim 30.

The reasons for allowance of claims 10, 15, 21 have been stated in the previous office actions (mailing date 7/8/2005 and 4/1/2006)

Art Unit: 1765

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

2. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lan Vinh whose telephone number is 571 272 1471. The examiner can normally be reached on M-F 8:30-5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571 272 1465. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

May 11, 2006